

# PBSS5230T

# 30 V, 2 A PNP low VCEsat (BISS) transistor Rev. 2 — 4 June 2012

**Product data sheet** 

#### 1. **Product profile**

## 1.1 General description

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a SOT23 small Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4230T.

#### 1.2 Features and benefits

- Low collector-emiter saturation voltage
- High collector current capability: I<sub>C</sub> and I<sub>CM</sub>
- Higher efficiency leading to less heat generation
- AEC-Q101 qualified

## 1.3 Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting

- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

#### 1.4 Quick reference data

Table 1. Quick reference data

| Symbol             | Parameter                               | Conditions  | Min | Тур | Max | Unit |
|--------------------|---|---|-----|-----|-----|------|
| $V_{CEO}$          | collector-emitter<br>voltage            | open base   | -   | -   | -30 | V    |
| I <sub>C</sub>     | collector current                       |   | -   | -   | -2  | Α    |
| I <sub>CM</sub>    | peak collector current                  | single pulse; t <sub>p</sub> ≤ 1 ms   | -   | -   | -3  | Α    |
| R <sub>CEsat</sub> | collector-emitter saturation resistance | $I_C$ = -500 mA; $I_B$ = -50 mA; pulsed;<br>$t_p \le 300 \ \mu s; \ \delta \le 0.02 \ ; \ T_{amb} = 25 \ ^{\circ}C$ | -   | 160 | 220 | Ω    |



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# 2. Pinning information

#### Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1   | В      | base        |                    |                |
| 2   | Е      | emitter     | 3                  | 3<br>          |
| 3   | С      | collector   | 1 2                | 1—             |
|     |        |             | SOT23 (TO-236AB)   | 2<br>sym013    |

# 3. Ordering information

Table 3. Ordering information

| Type number Package |          |  |         |
|---------------------|----------|--|---------|
|                     | Name     | Description                              | Version |
| PBSS5230T           | TO-236AB | plastic surface-mounted package; 3 leads | SOT23   |

## 4. Marking

Table 4. Marking codes

| Type number | Marking code <sup>[1]</sup> |
|-------------|-----------------------------|
| PBSS5230T   | %3G                         |

<sup>[1] % =</sup> placeholder for manufacturing site code

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter                 | Conditions                          |            | Min | Max  | Unit |
|------------------|---------------------------|-------------------------------------|------------|-----|------|------|
| $V_{CBO}$        | collector-base voltage    | open emitter                        |            | -   | -30  | V    |
| V <sub>CEO</sub> | collector-emitter voltage | open base                           |            | -   | -30  | V    |
| V <sub>EBO</sub> | emitter-base voltage      | open collector                      |            | -   | -5   | V    |
| I <sub>C</sub>   | collector current         |                                     |            | -   | -2   | Α    |
| I <sub>CM</sub>  | peak collector current    | single pulse; t <sub>p</sub> ≤ 1 ms |            | -   | -3   | Α    |
| I <sub>B</sub>   | base current              |                                     |            | -   | -300 | mA   |
| P <sub>tot</sub> | total power dissipation   | T <sub>amb</sub> ≤ 25 °C            | <u>[1]</u> | -   | 300  | mW   |
|                  |                           |                                     | [2]        | -   | 480  | mW   |
| Tj               | junction temperature      |                                     |            | -   | 150  | °C   |
| T <sub>amb</sub> | ambient temperature       |                                     |            | -65 | 150  | °C   |
| T <sub>stg</sub> | storage temperature       |                                     |            | -65 | 150  | °C   |

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

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## 6. Thermal characteristics

#### Table 6. Thermal characteristics

| Symbol        | Parameter                   | Conditions  |            | Min | Тур | Max | Unit |
|---------------|-----------------------------|-------------|------------|-----|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance          | in free air | <u>[1]</u> | -   | -   | 417 | K/W  |
|               | from junction to<br>ambient |             | <u>[2]</u> | -   | -   | 260 | K/W  |

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

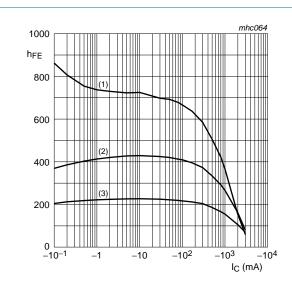
## 7. Characteristics

Table 7. Characteristics

| 0                  | Danamatan                               | 0  | NA! | T    | NA    | 11!1 |
|--------------------|---|--|-----|------|-------|------|
| Symbol             | Parameter                               | Conditions   | Min | Тур  | Max   | Unit |
| I <sub>CBO</sub>   | collector-base cut-off                  | $V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}; T_{amb} = 25 \text{ °C}$   | -   | -    | -100  | nΑ   |
|                    | current                                 | $V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$  | -   | -    | -50   | μΑ   |
| I <sub>EBO</sub>   | emitter-base cut-off current            | $V_{EB} = -4 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$  | -   | -    | -100  | nA   |
| h <sub>FE</sub>    | DC current gain                         | $V_{CE} = -2 \text{ V}; I_{C} = -100 \text{ mA}; T_{amb} = 25 \text{ °C}$  | 300 | 450  | -     |      |
|                    |   | $V_{CE} = -2 \text{ V; } I_{C} = -1 \text{ A; pulsed;}$<br>$t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$ | 200 | 290  | -     |      |
|                    |   | $V_{CE}$ = -2 V; $I_{C}$ = -2 A; pulsed;<br>$t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 \text{ °C}$                          | 100 | 180  | -     |      |
| V <sub>CEsat</sub> | collector-emitter saturation voltage    | $I_C$ = -500 mA; $I_B$ = -50 mA; $T_{amb}$ = 25 °C   | -   | -70  | -110  | mV   |
|                    |   | $I_C = -1 \text{ A}; I_B = -50 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$  | -   | -140 | -225  | mV   |
|                    |   | $I_C = -2 \text{ A}; I_B = -200 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$   | -   | -240 | -350  | mV   |
| R <sub>CEsat</sub> | collector-emitter saturation resistance | $I_{C}$ = -500 mA; $I_{B}$ = -50 mA; pulsed;<br>$t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$            | -   | 160  | 220   | Ω    |
| V <sub>BEsat</sub> | base-emitter saturation voltage         | $I_C$ = -2 A; $I_B$ = -50 mA; pulsed;<br>$t_p \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb} = 25 °C$                                       | -   | -    | -1.1  | V    |
| $V_{BEon}$         | base-emitter turn-on voltage            | $V_{CE} = -2 \text{ V}; I_{C} = -100 \text{ mA}; T_{amb} = 25 \text{ °C}$  | -   | -    | -0.75 | V    |
| f⊤                 | transition frequency                    | $V_{CE} = -10 \text{ V}; I_{C} = -100 \text{ mA};$<br>f = 100 MHz; $T_{amb} = 25 \text{ °C}$   | 100 | 200  | -     | MHz  |
| C <sub>c</sub>     | collector capacitance                   | $V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$<br>f = 1 MHz; $T_{amb} = 25 \text{ °C}$                                    | -   | 23   | 28    | pF   |

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

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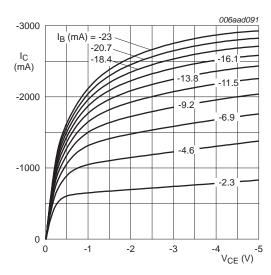
$$V_{CE} = -2 V$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

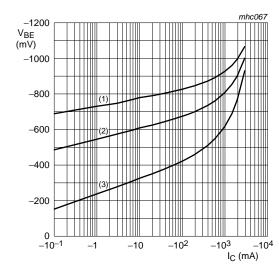
(3) 
$$T_{amb} = -55$$
 °C

Fig 1. DC current gain as a function of collector current; typical values



T<sub>amb</sub> = 25 °C

Fig 2. Collector current as a function of collector-emitter voltage; typical values



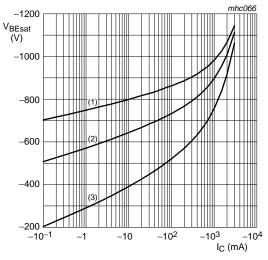
 $V_{CE} = -2 V$ 

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 3. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

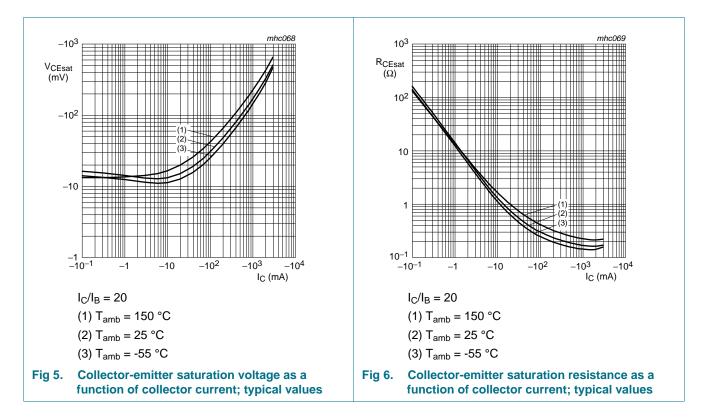
(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 4. Base-emitter saturation voltage as a function of collector current; typical values

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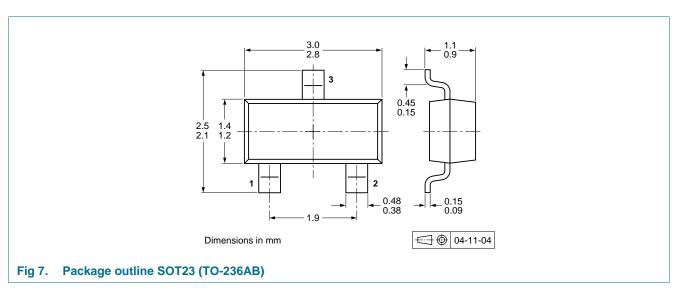


## 8. Test information

## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 9. Package outline



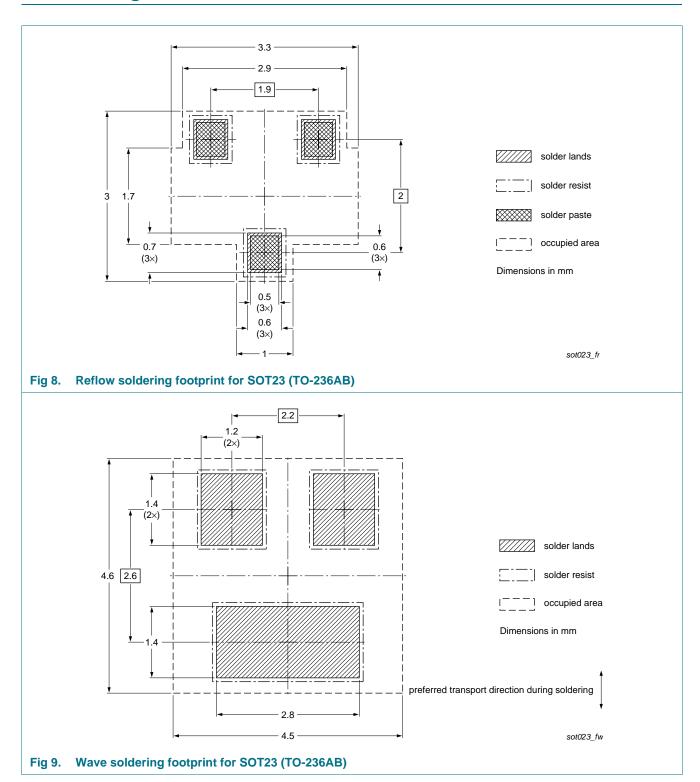
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## 30 V, 2 A PNP low VCEsat (BISS) transistor

# 10. Soldering



## 30 V, 2 A PNP low VCEsat (BISS) transistor

# 11. Revision history

## Table 8. Revision history

| Document ID  | Release date   | Data sheet status   | Change notice            | Supersedes                    |  |  |
|--|--|---|--------------------------|-------------------------------|--|--|
| PBSS5230T v.2  | 20120604   | Product data sheet  | -                        | PBSS5230T v.1                 |  |  |
| Modifications:   | <ul> <li>The format of the NXP Semiconor</li> </ul>                                    |   | esigned to comply with t | he new identity guidelines of |  |  |
| <ul> <li>Legal texts have been adapted to the new company name where appropr</li> <li><u>1 "Product profile"</u>: updated</li> </ul> |  |   |                          | appropriate.                  |  |  |
|  |  |   |                          |                               |  |  |
|  | • <u>4 "Marking"</u> : corrected   |   |                          |                               |  |  |
|  | • <u>Table 5.</u> : updated  |   |                          |                               |  |  |
|  | <ul> <li>7 "Characteris</li> </ul>   | <ul> <li><u>7 "Characteristics"</u>: V<sub>CEsat</sub> corrected, <u>Fig 1.</u> to <u>Fig 6.</u> added</li> </ul> |                          |                               |  |  |
|  | <ul> <li>8 "Test information": added</li> </ul>  |   |                          |                               |  |  |
|  | <ul> <li>9 "Package outline": replaced by minimized package outline drawing</li> </ul> |   |                          |                               |  |  |
|  | • 10 "Soldering"   | : added   |                          |                               |  |  |
| PBSS5230T v.1  | 20031218   | Product data sheet  | -                        | -                             |  |  |

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## 12. Legal information

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| Document status[1] [2]         | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
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